

AMENDMENTS TO THE SPECIFICATION

- Please amend the paragraph in the BEST MODE FOR CARRYING OUT THE INVENTION, which begins on page 12, line 25, as follows:

Referring now to FIG. 22B therein is shown a cross sectional view taken along line 22B-22B of FIG. ~~21A~~. 21. The emitter contact 2100 is formed by etching the third insulating layer 1222 to stop on the extrinsic emitter structure 1220A. The base contact is formed by etching the third insulating layer 1222, the extrinsic emitter structure 1220A and the second insulating layer 1218 to stop on the extrinsic base structure 1216A.

- Please amend the paragraph in the BEST MODE FOR CARRYING OUT THE INVENTION, which begins on page 13, line 12, as follows:

Referring now to FIG. 24, therein is shown the structure of FIG. 23 after formation of a fifth insulating layer 2400, such as a TEOS layer. The fifth insulating layer 2400 is formed by filling the first trench 2310 and the second trench 2311 with a high-density plasma (HDP) oxide or TEOS ~~later~~. layer. The fifth insulating layer 2400 then undergoes a chemical-mechanical polish (CMP) and then is recessed deep into the first trench 2310 and the second trench 2311 by etching.